

ABSTRACT OF THE DISCLOSURE

The invention includes a photolithographic method in which overlapping first and second exposure patterns are formed on a photosensitive material from light passed through a single reticle. The first exposure pattern of the radiation comprises features separated by about a minimum feature spacing that can be accomplished with a single reticle exposure at the time of the photolithographic processing, and the overlapping first and second patterns comprise features separated by less than the minimum feature spacing. The invention also includes a photolithographic method of forming overlapping exposure patterns on a photosensitive material from light passed through a single reticle wherein the reticle is moved between a first exposure to a first light and a second exposure to a second light.